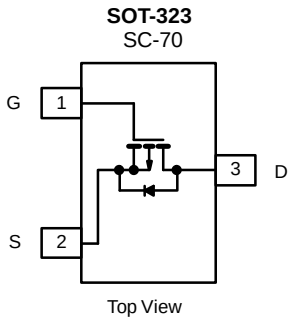
P-Channel 60 V (D-S) MOSFET

PRODUCT SUMMARY			
V_{DS} (V)	$R_{DS(on)}$ (Ω)	$V_{GS(th)}$ (V)	I_D (mA)
- 60	4 at V_{GS} = - 10 V	- 1 to - 3	- 135



FEATURES

- **Halogen-free According to IEC 61249-2-21 Definition**
- TrenchFET® Power MOSFET
- High-Side Switching
- Low On-Resistance: 4 Ω
- Low Threshold: - 2 V (typ.)
- Fast Swtiching Speed: 20 ns (typ.)
- Low Input Capacitance: 20 pF (typ.)
- Compliant to RoHS Directive 2002/95/EC

Pb-free
RoHS COMPLIANT
HALOGEN FREE Available

APPLICATIONS

- Drivers: Relays, Solenoids, Lamps, Hammers, Display, Memories, Transistors, etc.
- Battery Operated Systems
- Power Supply Converter Circuits
- Solid-State Relays

BENEFITS

- Ease in Driving Switches
- Low Offset (Error) Voltage
- Low-Voltage Operation
- High-Speed Circuits
- Easily Driven without Buffer

ABSOLUTE MAXIMUM RATINGS T_A = 25 °C, unless otherwise noted				
Parameter		**Symbol**	**Limit**	**Unit**
Drain-Source Voltage		V_{DS}	- 60	V
Gate-Source Voltage		V_{GS}	± 20	
Continuous Drain Current[a]	T_A = 25 °C	I_D	- 135	mA
	T_A = 100 °C		- 105	
Pulsed Drain Current[b]		I_{DM}	- 800	
Power Dissipation[a]	T_A = 25 °C	P_D	350	mW
	T_A = 100 °C		140	
Maximum Junction-to-Ambient[a]		R_{thJA}	350	°C/W
Operating Junction and Storage Temperature Range		T_J, T_{stg}	- 55 to 150	°C

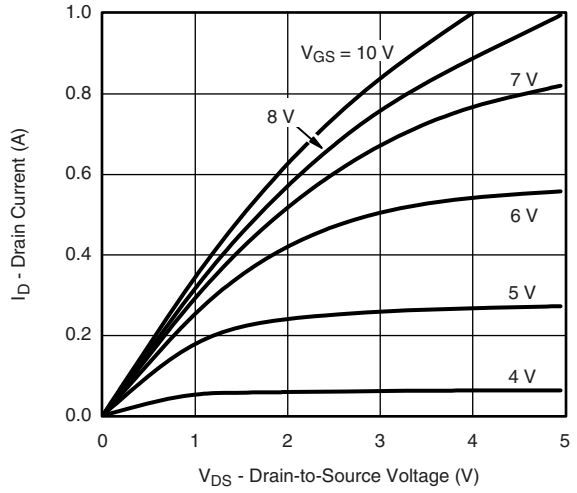
Notes:
a. Surface mounted on FR4 board.
b. Pulse width limited by maximum junction temperature.

SPECIFICATIONS T_A = 25 °C, unless otherwise noted						
			Limits			
Parameter	**Symbol**	**Test Conditions**	**Min.**	**Typ.[a]**	**Max.**	**Unit**
Static						
Drain-Source Breakdown Voltage	V_{DS}	V_{GS} = 0 V, I_D = - 10 µA	- 60			V
Gate-Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = - 250 µA	- 1		- 3	
Gate-Body Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ± 20 V			± 10	µA
		V_{DS} = 0 V, V_{GS} = ± 10 V			± 200	nA
		V_{DS} = 0 V, V_{GS} = ± 10 V, T_J = 85 °C			± 500	
		V_{DS} = 0 V, V_{GS} = ± 5 V			± 100	
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = - 60 V, V_{GS} = 0 V			- 25	
		V_{DS} = - 60 V, V_{GS} = 0 V, T_J = 85 °C			- 250	
On-State Drain Current[a]	$I_{D(on)}$	V_{GS} = - 10 V, V_{DS} = - 4.5 V	- 50			mA
		V_{GS} = - 10 V, V_{DS} = - 10 V	- 600			
Drain-Source On-Resistance[a]	$R_{DS(on)}$	V_{GS} = - 4.5 V, I_D = - 25 mA		5		Ω
		V_{GS} = - 10 V, I_D = - 100 mA		4		
		V_{GS} = - 10 V, I_D = - 100 mA, T_J =125 °C			9	
Forward Transconductance[a]	g_{fs}	V_{DS} = - 10 V, I_D = - 100 mA	80			mS
Diode Forward Voltage	V_{SD}	I_S = - 100 mA, V_{GS} = 0 V			- 1.4	V
Dynamic						
Total Gate Charge	Q_g	V_{DS} = - 30 V, V_{GS} = - 15 V $I_D \cong$ - 100 mA		1.7		nC
Gate-Source Charge	Q_{gs}			0.26		
Gate-Drain Charge	Q_{gd}			0.46		
Input Capacitance	C_{iss}	V_{DS} = - 25 V, V_{GS} = 0 V f = 1 MHz		23		pF
Output Capacitance	C_{oss}			10		
Reverse Transfer Capacitance	C_{rss}			5		
Switching[b]						
Turn-On Time	$t_{d(on)}$	V_{DD} = - 25 V, R_L = 150 Ω $I_D \cong$ - 200 mA, V_{GEN} = - 10 V, R_g = 10 Ω		20		ns
Turn-Off Time	$t_{d(off)}$			35		

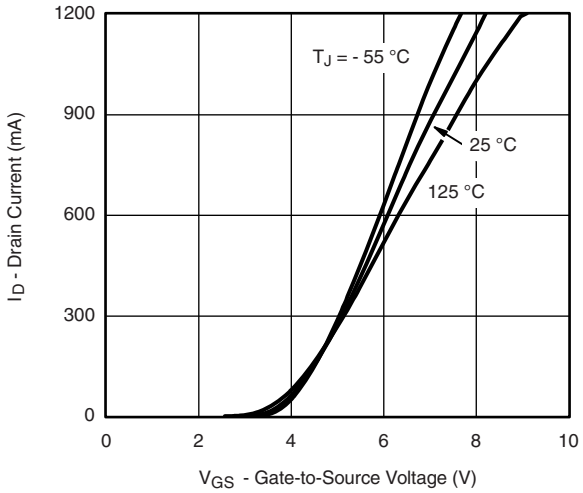
Notes:
a. Pulse test: PW ≤ 300 µs duty cycle ≤ 2 %.
b. Switching time is essentially independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

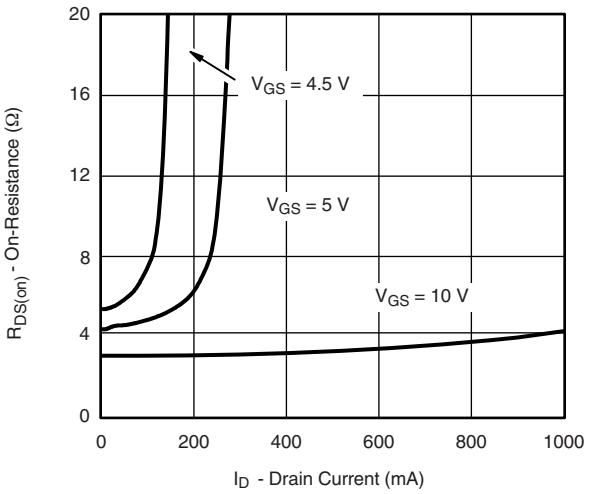
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



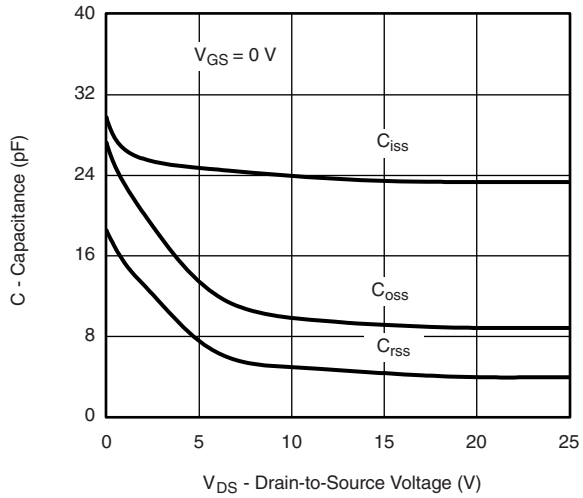
Output Characteristics



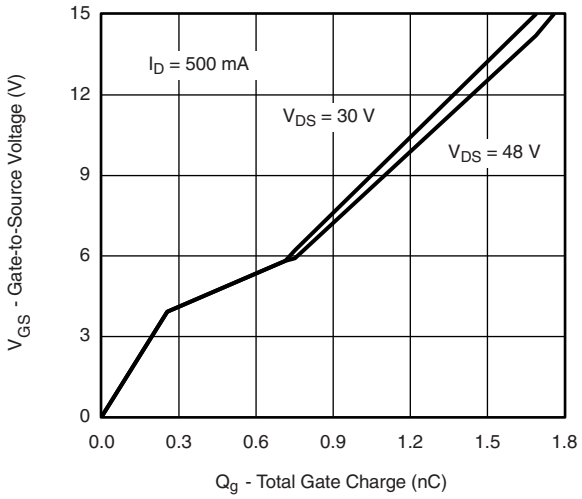
Transfer Characteristics



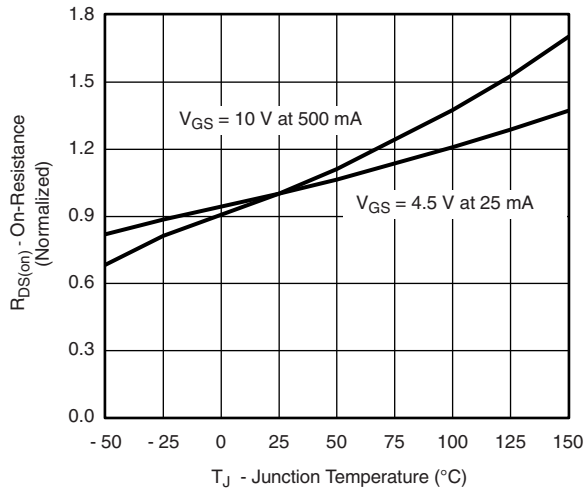
On-Resistance vs. Drain Current



Capacitance

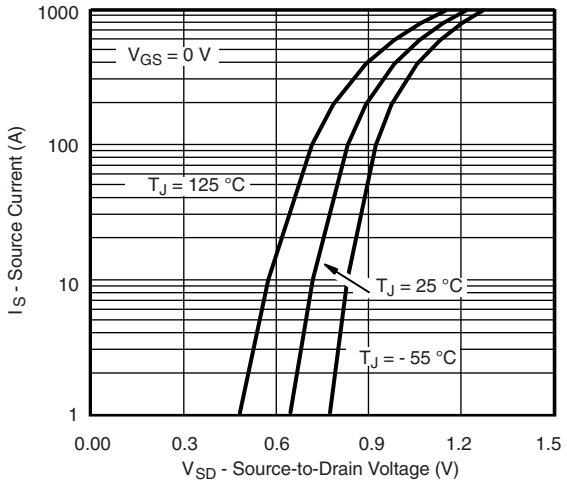


Gate Charge

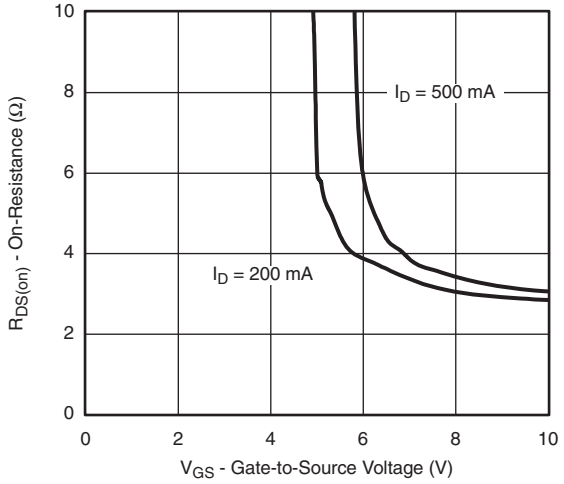


On-Resistance vs. Junction Temperature

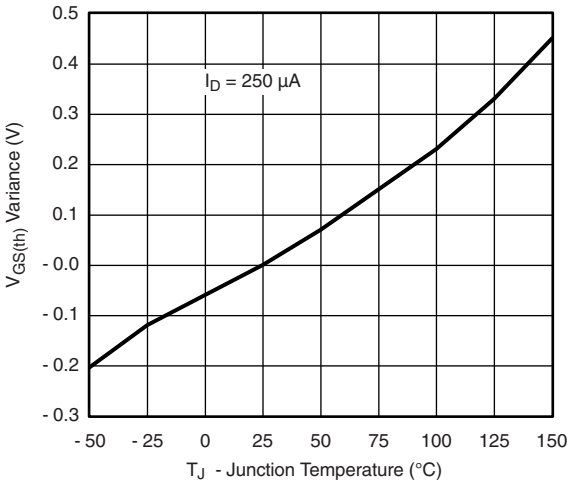
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



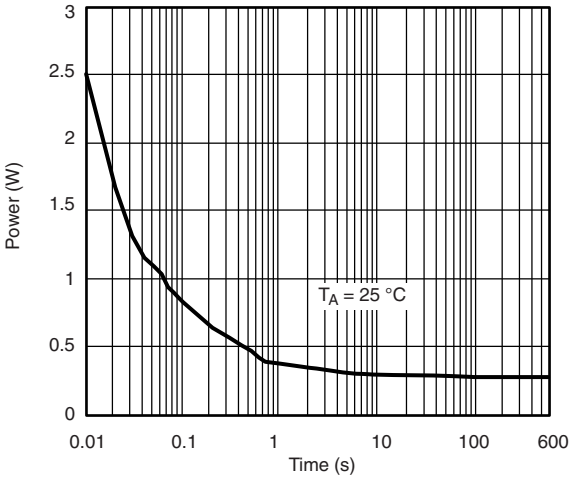
Source-Drain Diode Forward Voltage



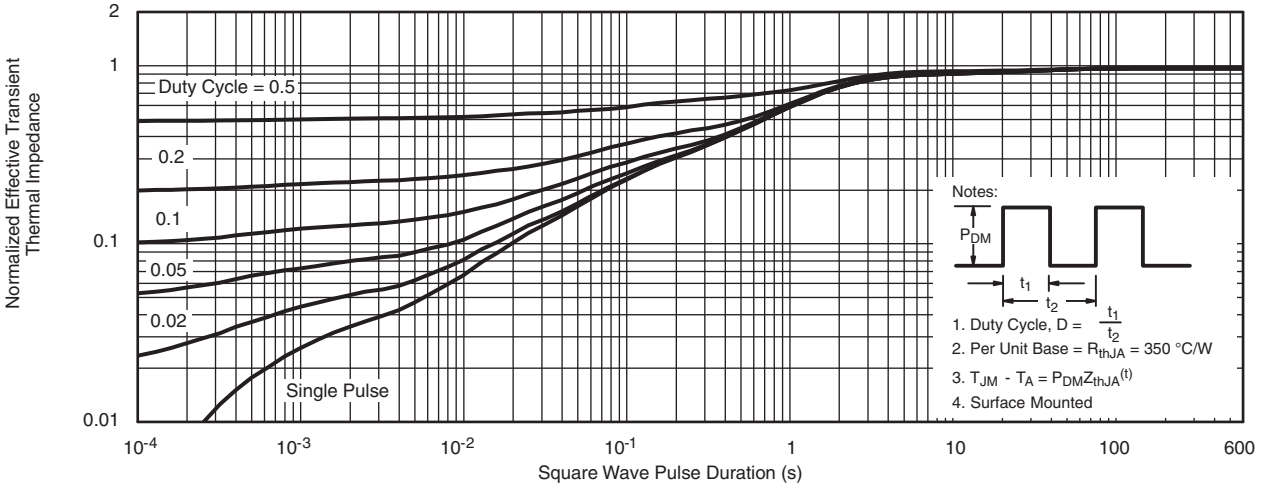
On-Resistance vs. Gate-Source Voltage



Threshold Voltage Variance Over Temperature

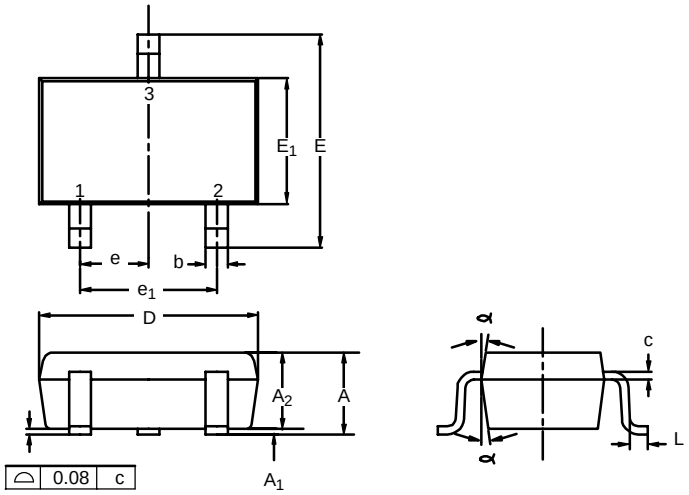


Single Pulse Power, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Ambient

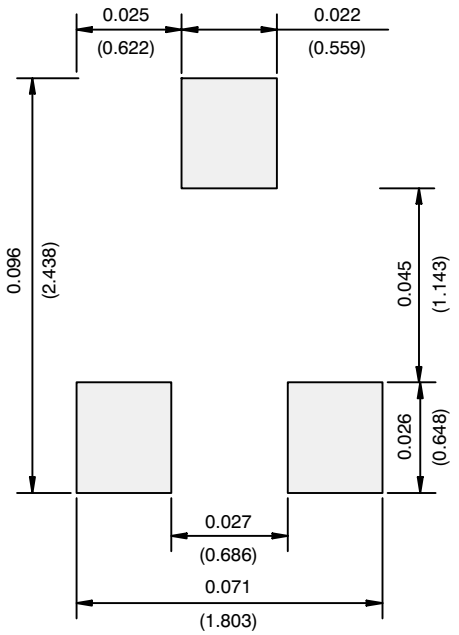
SC-70: 3-LEADS



Dim	MILLIMETERS			INCHES		
	Min	Nom	Max	Min	Nom	Max
A	0.90	–	1.10	0.035	–	0.043
A_1	–	–	0.10	–	–	0.004
A_2	0.80	–	1.00	0.031	–	0.039
b	0.25	–	0.40	0.010	–	0.016
c	0.10	–	0.25	0.004	–	0.010
D	1.80	2.00	2.20	0.071	0.079	0.087
E	1.80	2.10	2.40	0.071	0.083	0.094
E_1	1.15	1.25	1.35	0.045	0.049	0.053
e	0.65BSC			0.026BSC		
e_1	1.20	1.30	1.40	0.047	0.051	0.055
L	0.10	0.20	0.30	0.004	0.008	0.012
∝	7°Nom			7°Nom		

ECN: S-03946—Rev. C, 09-Jul-01
DWG: 5549

RECOMMENDED MINIMUM PADS FOR SC-70: 3-Lead



Recommended Minimum Pads
Dimensions in Inches/(mm)

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